

DUAL OPERATIONAL AMPLIFIER

GENERAL DESCRIPTION

The NJM4558/4559 integrated circuit are a dual high-gain operational amplifier internally compensated and constructed on a single silicon chip using an advanced epitaxial process.

Combining the features of the NJM741 with the close parameter matching and tracking of a dual device on a monolithic chip results in unique performance characteristics. Excellent channel separation allow the use of the dual device in single NJM741 operational amplifier applications providing density. It is especially well suited for applications in differential-in, differential-out as well as in potentiometric amplifiers and where gain and phase matched channels are mandatory.

FEATURES

Operating Voltage

 $(\pm 4V \sim \pm 18V)$

High Voltage Gain

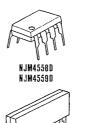
(100dB typ.)

High Input Resistance Package Outline

 $(5M\Omega \text{ typ.})$ DIP8, DMP8, SIP8, SSOP8

Bipolar Technology

PACKAGE OUTLINE



NJM4558L

NJM4559L

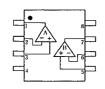


NJM4558M NJM4559M

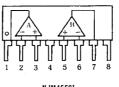


NJM4558V NJM4559V

PIN CONFIGURATION



NJM4558D, NJM4558M, NJM4558V NJM4559D, NJM4559M, NJM4559V

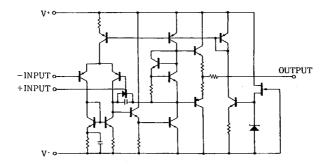


NJM4558L NJM4559L

PIN FUNCTION

- 1. A OUTPUT
- 2 . A-INPUT
- 3. A+INPUT
- 4 . V 5. B+INPUT
- 6. B-INPUT
- 7. B OUTPUT
- 8. V+

■ EQUIVALENT CIRCUIT (1/2 Shown)



■ ABSOLUTE MAXIMUM RATINGS

(Ta=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT	
Supply Voltage	V+/V-	±18		
Differential Input Voltage	V _{ID}	±30 ,	V	
Input Voltage	V _{1C} ±15 (note)		V	
Power Dissipation		(DIP8) 500	mW	
	Po	(DMP8) 300	mW	
		(SSOP8) 250	mW	
		(SIP8) 800	mW	
Operating Temperature Range	Topr	Topr -40~+85		
Storage Temperature Range	T _{stg}	-40~+125	℃	

(note) For supply voltage less than $\pm 15V$, the absolute maximum input voltage is equal to the supply voltage.

■ ELECTRICAL CHARACTERISTICS

 $(V^{+}/V^{-}=\pm 15V \text{ Ta}=25^{\circ}C)$

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Offset Voltage	Vio	$R_s \leq 10 k\Omega$	_	0.5	6	mV
Input Offset Current	lio		-	5	200	nA
Input Bias Current	I_{B}	·	—	25	500	nA
Input Resistance	R _{IN}		0.3	5		ΜΩ
Large Signal Voltage Gain	Av	$R_L \ge 2k\Omega$, $V_O = \pm 10V$	86	100		dB
Maximum Output Voltage Swing 1	V _{OM1}	R _L ≥ 10kΩ	土12	±14	—	V
Maximum Output Voltage Swing 2	V _{OM2}	$R_L \ge 2\Omega$	±10	±13	—	V
Input Common Mode Voltage Range	V _{ICM}		±12	14		V
Common Mode Rejection Ratio	CMR	$R_S \leq 10k\Omega$	70	90	_	dB
Supply Voltage Rejection Ratio	SVR	$R_S \leq 10k\Omega$. 76.5	90		dB
Operating Current	Icc		—	3.5	5.7	mA
Slew Rate						1
NJM4558	SR		_	1		V/μS
NJM4559	SR		_	2	_	V/μS
Equivalent Input Noise Voltage	V _{NI}	RIAA, $R_S = 1k\Omega$, 30kHz LPF		1.4	—	μVrms
Gain Bandwidth Product	GB	•				
NJM4558	1			3	1	MHz
NJM4559				6	1	MHz